

MMBC1622D8

NPN EPITAXIAL SILICON TRANSISTOR

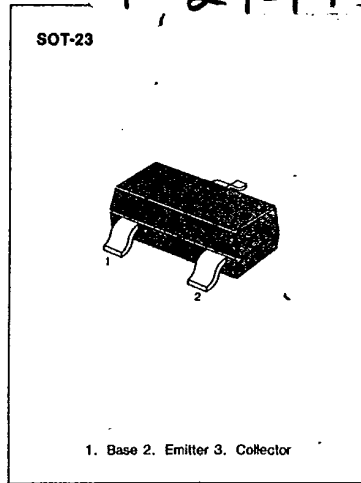
AMPLIFIER TRANSISTOR

T-29-19

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

| Characteristic | Symbol | Rating | Unit |
|---------------------------|------------------|--------|------|
| Collector-Base Voltage | V _{CB0} | 40 | V |
| Collector-Emitter Voltage | V _{CE0} | 35 | V |
| Emitter-Base Voltage | V _{EB0} | 5.0 | V |
| Collector Current | I _C | 100 | mA |
| Collector Dissipation | P _C | 350 | mW |
| Storage Temperature | T _{stg} | 150 | °C |

• Refer to MMBC1622D6 for graphs



ELECTRICAL CHARACTERISTICS (T_a = 25°C)

| Characteristic | Symbol | Test Condition | Min | Max | Unit |
|--------------------------------------|-----------------------|--|------|------|------|
| Collector Cutoff Current | I _{CB0} | V _{CB} =25V, I _E =0 | | 50 | nA |
| Emitter Cutoff Current | I _{EB0} | V _{EB} =5V, I _C =0 | | 50 | nA |
| DC Current Gain | h _{FE} | V _{CE} =3V, I _C =0.1mA | 150 | | |
| | | V _{CE} =3V, I _C =0.5mA | 450 | 900 | |
| Collector-Emitter Saturation Voltage | V _{CE (sat)} | I _C =100mA, I _B =10mA | | 0.3 | V |
| Base-Emitter On Voltage | V _{BE (on)} | I _C =0.5mA, V _{CE} =3V | 0.55 | 0.65 | V |
| Current Gain-Bandwidth Product | f _T | V _{CE} =6V, I _E =1mA f=100MHz | 100 | | MHz |

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Marking

